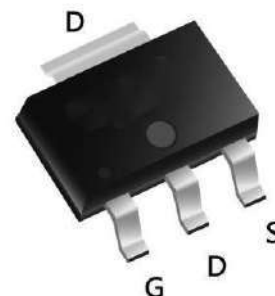


N-Ch 60V Fast Switching MOSFETs

Features:

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

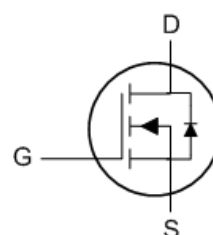


Description:

The KL6008 is the high cell density trench N-ch MOSFETs, which provides excellent $R_{DS(on)}$ and efficiency for most of the small power switching and load switch applications.

The KL6008 meet the RoHS and Green Product requirement with full function reliability approved.

SOT223 Pin Configuration



Product Summary

BVDSS	$R_{DS(on)}$	I_D
60V	100m Ω	2.8A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	2.8	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	2.3	A
I_{DM}	Pulsed Drain Current ²	12	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	48	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.054	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =2.5A	---	80	100	mΩ
		V _{GS} =4.5V, I _D =2A	---	85	110	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.96	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =2A	---	13	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =48V, V _{GS} =4.5V, I _D =2A	---	5	7.0	nC
Q _{gs}	Gate-Source Charge		---	1.68	2.4	
Q _{gd}	Gate-Drain Charge		---	1.9	2.7	
T _{d(on)}	Turn-On Delay Time	V _{DS} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =2A	---	1.6	3.2	ns
T _r	Rise Time		---	7.2	13	
T _{d(off)}	Turn-Off Delay Time		---	25	50	
T _f	Fall Time		---	14.4	28.8	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	511	715	pF
C _{oss}	Output Capacitance		---	38	53	
C _{rss}	Reverse Transfer Capacitance		---	25	35	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	2.8	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	12	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =2A, dI/dt=100A/μs, T _J =25°C	---	9.7	---	nS
Q _{rr}	Reverse Recovery Charge		---	5.8	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3. The power dissipation is limited by 150°C junction temperature

4. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

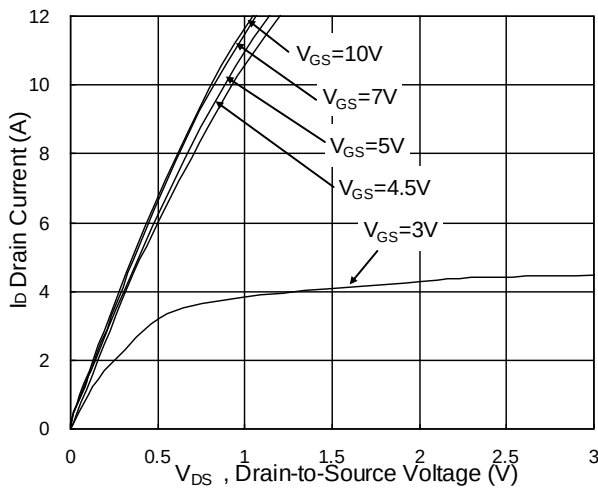


Fig.1 Typical Output Characteristics

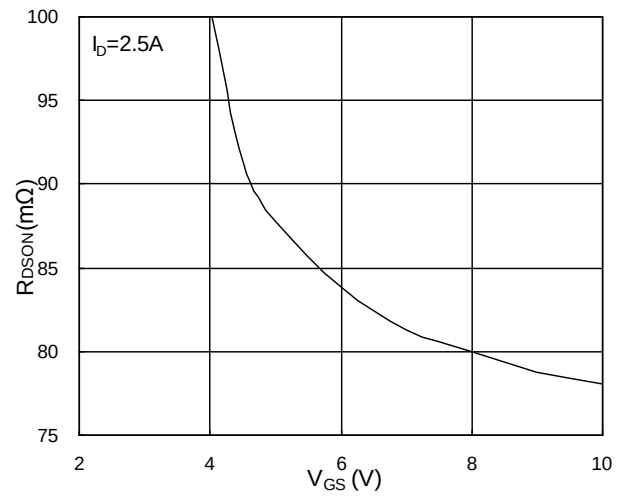


Fig.2 On-Resistance v.s Gate-Source

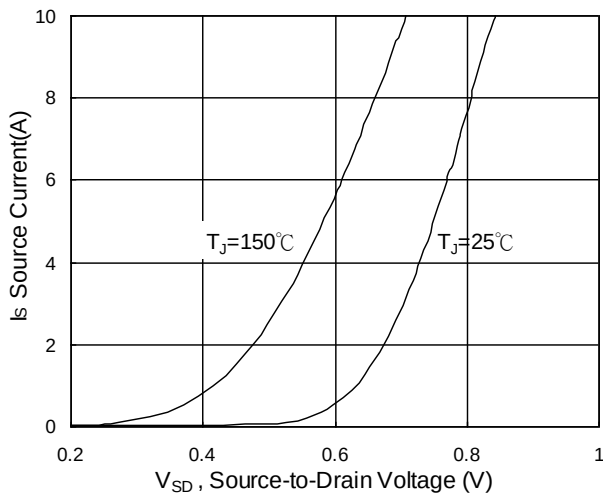


Fig.3 Forward Characteristics of Reverse

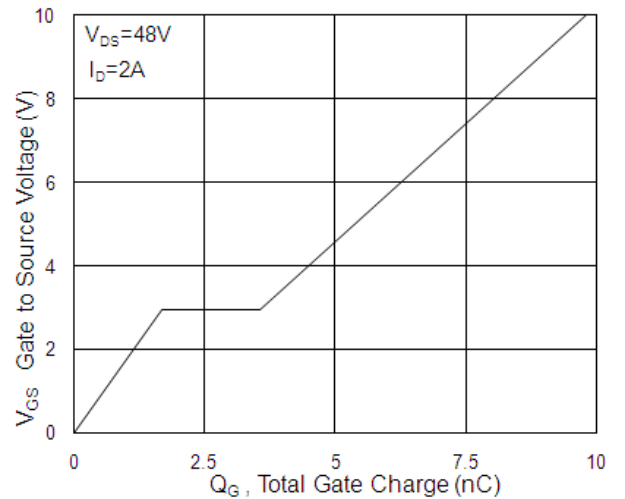


Fig.4 Gate-Charge Characteristics

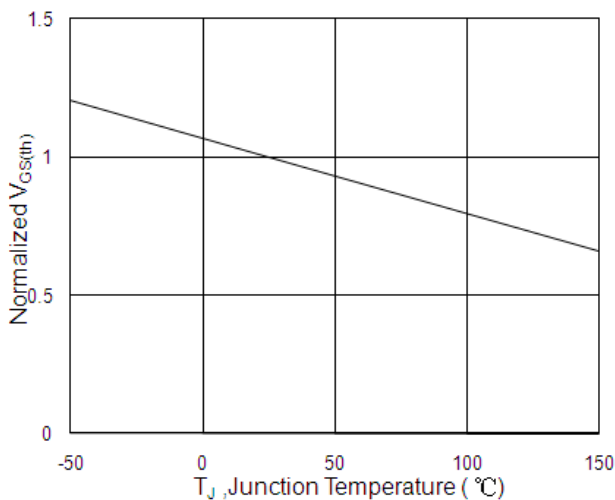


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

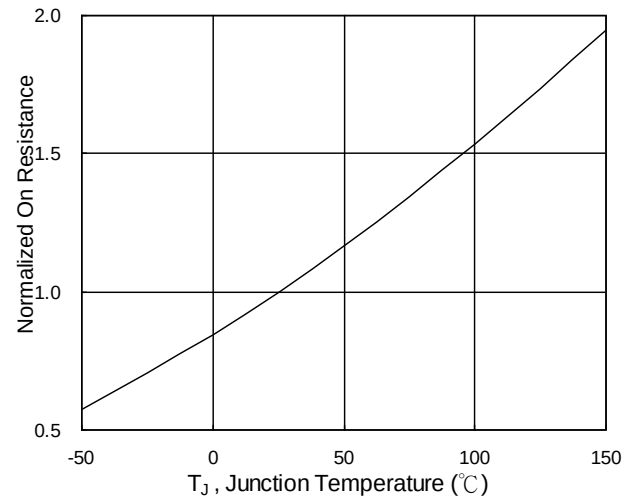


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

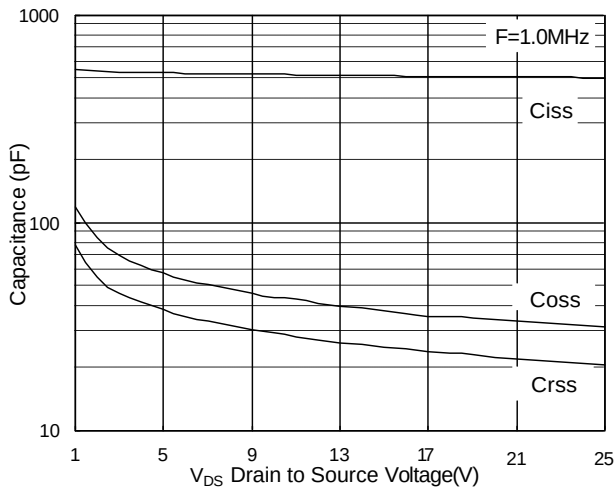


Fig.7 Capacitance

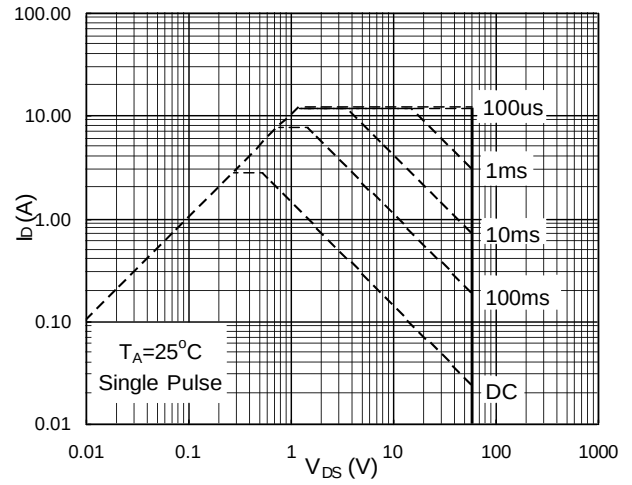


Fig.8 Safe Operating Area

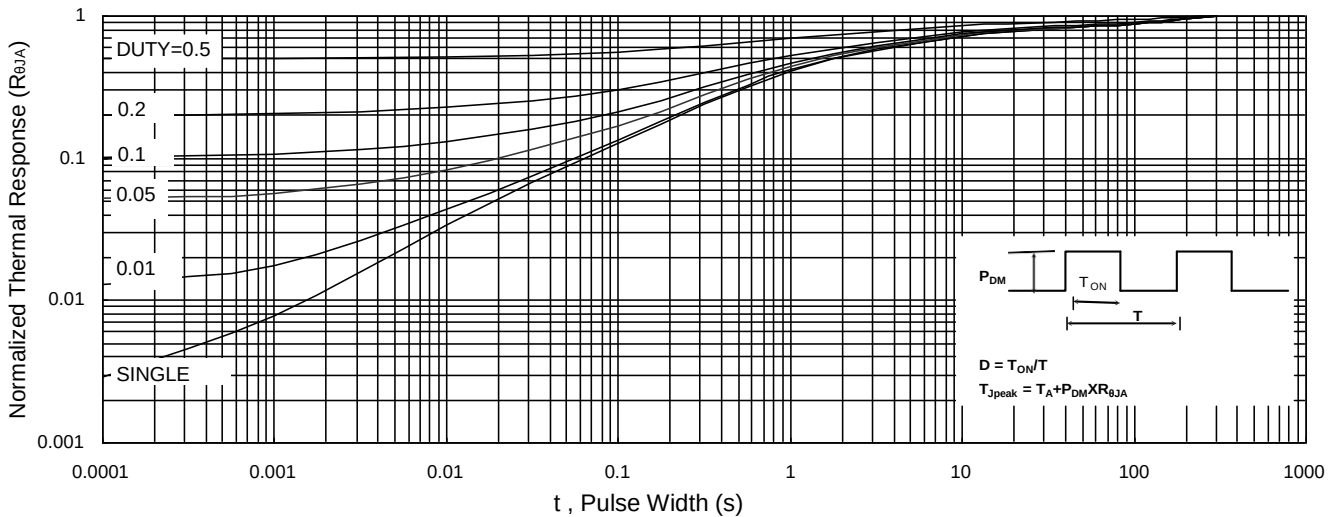


Fig.9 Normalized Maximum Transient Thermal Impedance

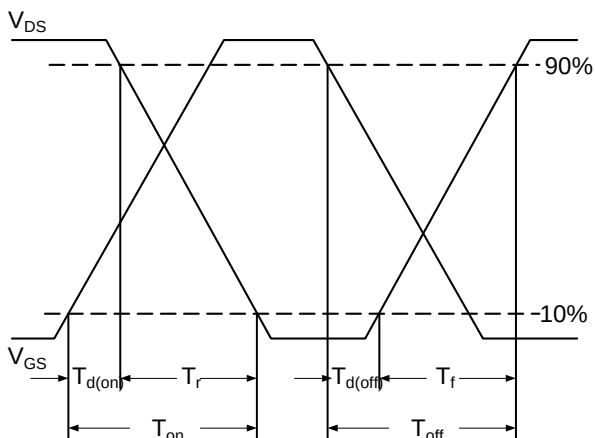


Fig.10 Switching Time Waveform

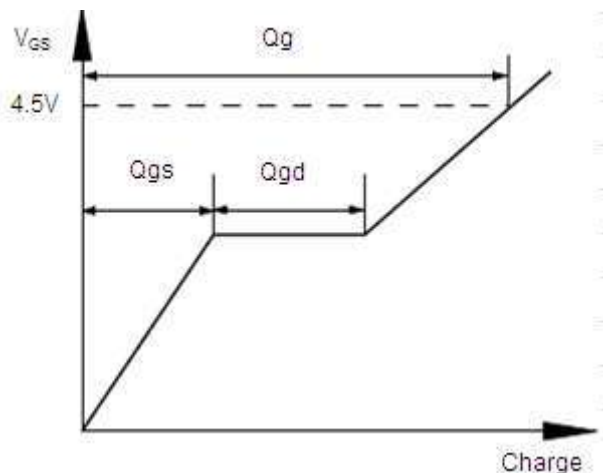
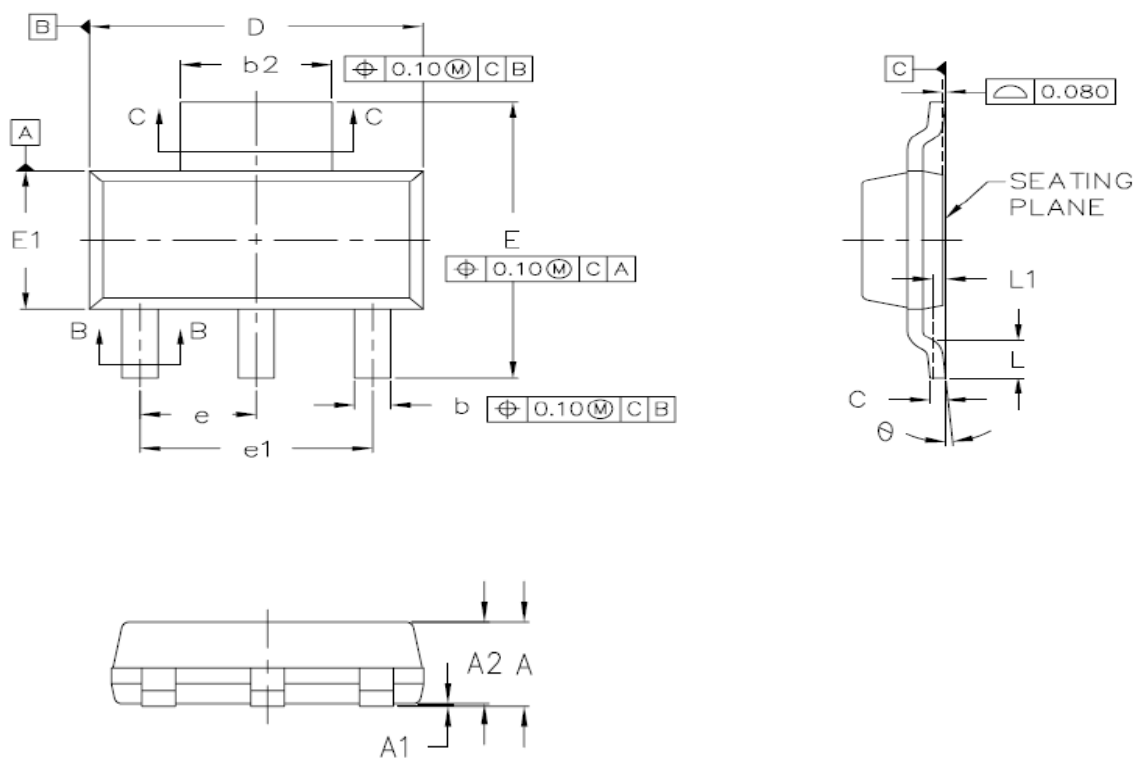


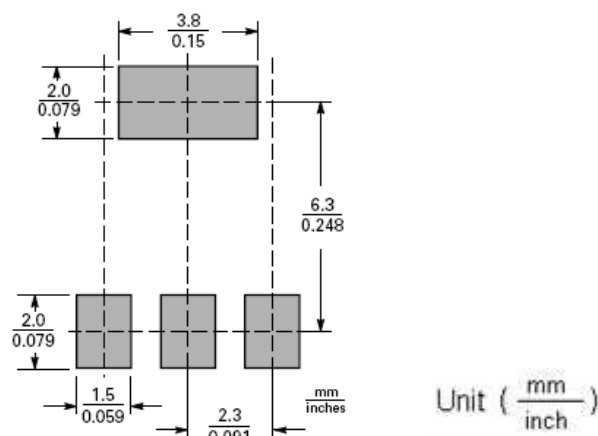
Fig.11 Gate Charge Waveform

SOT-223 Package Outline

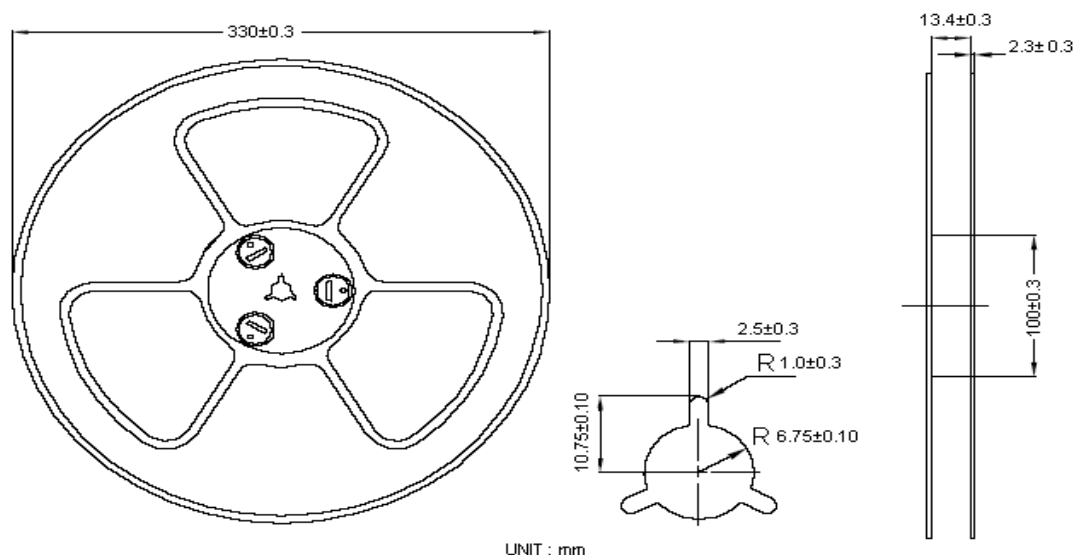


SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	—	1.80	—	0.071
A1	0.02	0.10	0.001	0.004
A2	1.50	1.70	0.059	0.067
b	0.66	0.84	0.026	0.033
b1	0.60	0.79	0.024	0.031
b2	2.90	3.10	0.114	0.122
b3	2.84	3.05	0.112	0.120
c	0.23	0.35	0.009	0.014
c1	0.23	0.33	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.30 BSC.		0.091 BSC.	
e1	4.60 BSC.		0.182 BSC.	
L	0.81	—	0.032	—
L1	0.25 BSC.		0.010 BSC.	
θ	0°	10°	0°	10°

Recommended Soldering Footprint



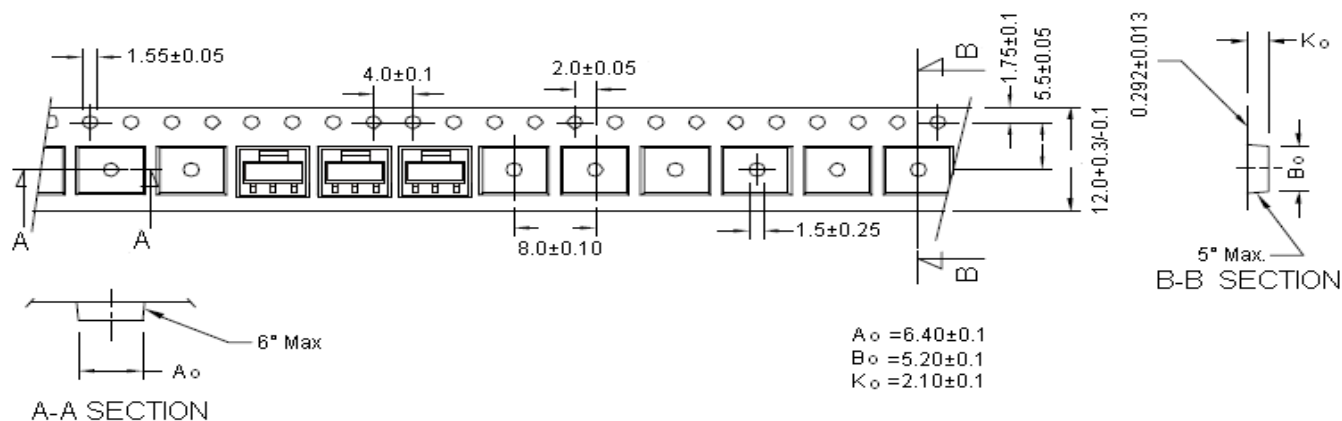
Reel Dimension



UNIT : mm

NOTE : 1. Material : Anti-static polystyrene
2. Surface resistivity $10^9 \Omega/\text{sq}$

Carrier Tape Dimension



Notes:

1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Uni : millimeter